

Transient Voltage Suppressors

ESD Protection Diodes with Ultra-Low Capacitance

The ESD5L is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.

Specification Features:

- Ultra Low Capacitance 0.5 pF
- Low Clamping Voltage
- Stand-off Voltage: 3.3 V
- Low Leakage
- Response Time is Typically < 1.0 ns
- IEC61000-4-2 Level 4 ESD Protection
- This is a Pb-Free Device
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

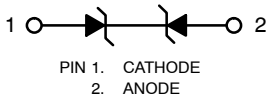
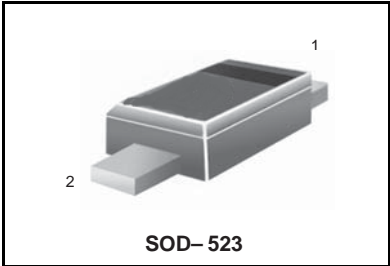
Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic
Epoxy Meets UL 94 V-0

LEAD FINISH: 100% Matte Sn (Tin)

QUALIFIED MAX REFLOW TEMPERATURE: 260°C

Device Meets MSL 1 Requirements



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		± 10 ± 15	kV
Total Power Dissipation on FR-5 Board (Note 1) @ $T_A = 25^{\circ}\text{C}$	P_D	200	mW
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Junction Temperature Range	T_J	-55 to +125	$^{\circ}\text{C}$
Lead Solder Temperature - Maximum (10 Second Duration)	T_L	260	$^{\circ}\text{C}$

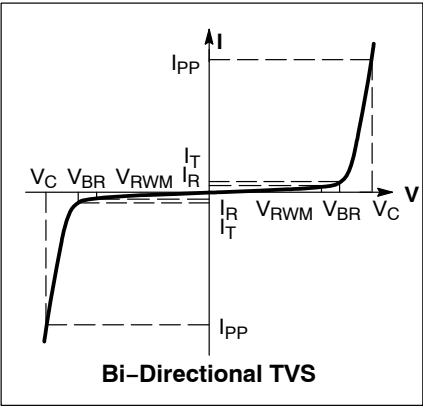
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
I _F	Forward Current
V _F	Forward Voltage @ I _F
P _{pk}	Peak Power Dissipation
C	Capacitance @ V _R = 0 and f = 1.0 MHz



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Device	Device Marking	V _{RWM} (V)	I _R (μA) @ V _{RWM}	V _{BR} (V) @ I _T (Note 2)	I _T	C (pF)		V _C (V) @ I _{PP} = 1 A (Note 3)	V _C
		Max	Max	Min	mA	Typ	Max	Max	Per IEC61000-4-2 (Note 4)
ESD5L3.3C	SL	3.3	1.0	4.8	1.0	0.5	0.9	10	Figures 1 and 2 See Below

- V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.
- Surge current waveform per Figure 4.
- For test procedure see Figures 3.

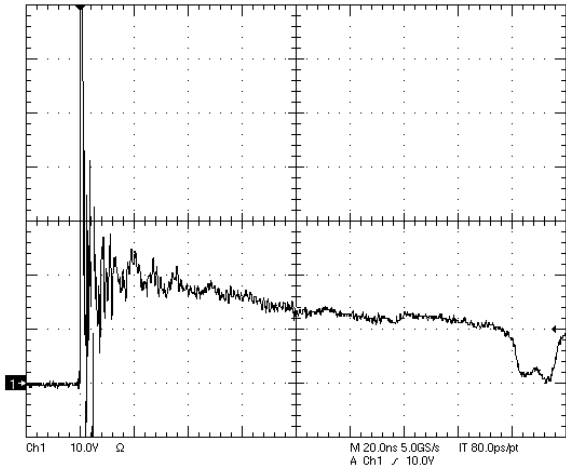


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

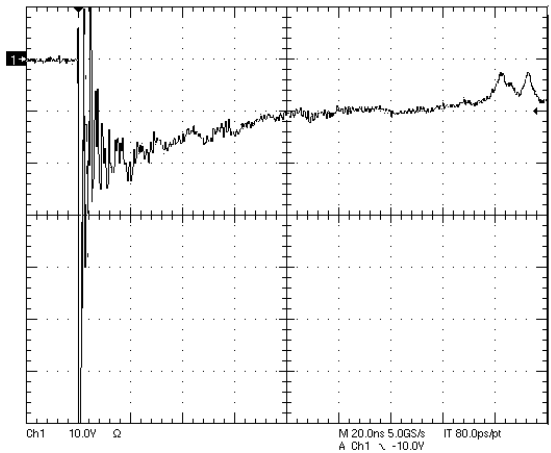


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

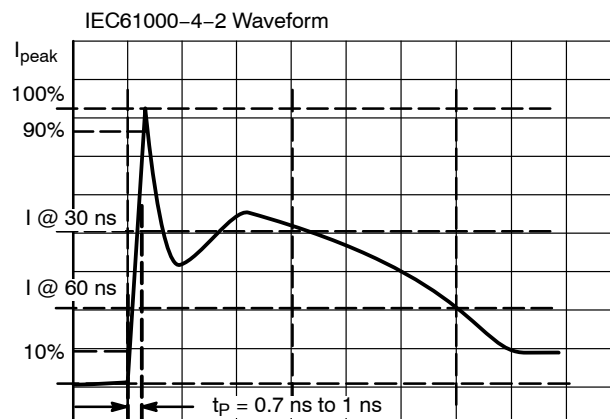


Figure 3. IEC61000-4-2 Spec

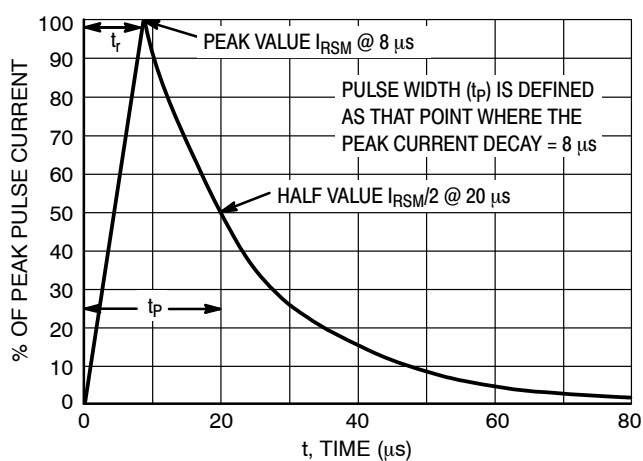
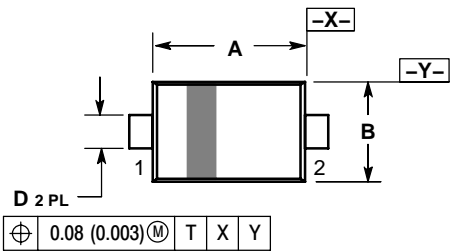


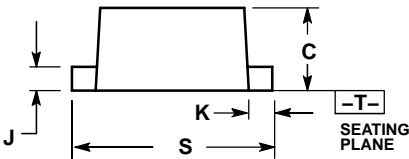
Figure 4. 8 X 20 μs Pulse Waveform

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- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.10	1.20	1.30	0.043	0.047	0.051
B	0.70	0.80	0.90	0.028	0.032	0.035
C	0.50	0.60	0.70	0.020	0.024	0.028
D	0.25	0.30	0.35	0.010	0.012	0.014
J	0.07	0.14	0.20	0.0028	0.0055	0.0079
K	0.15	0.20	0.25	0.006	0.008	0.010
S	1.50	1.60	1.70	0.059	0.063	0.067



SOLDERING FOOTPRINT*

